

< IGBT MODULES >

CM150RX-24S1

HIGH POWER SWITCHING USE
INSULATED TYPE



sevenpack (3φ Inverter+Chopper Brake)

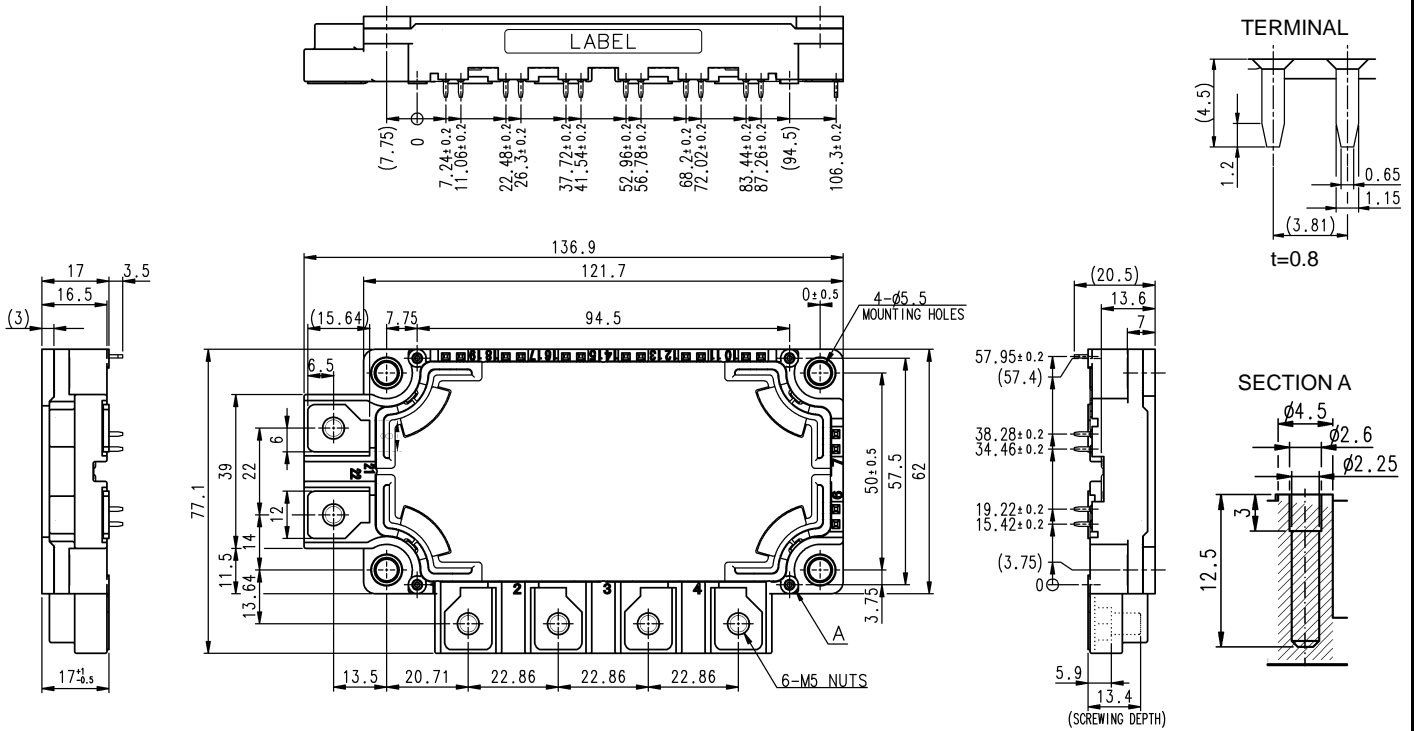
Collector current I_C **150 A**
 Collector-emitter voltage V_{CES} **1200 V**
 Maximum junction temperature T_{jmax} **175 °C**

- Flat base Type
- Copper base plate (non-plating)
- Tin plating pin terminals
- RoHS Directive compliant
- Recognized under UL1557, File E323585

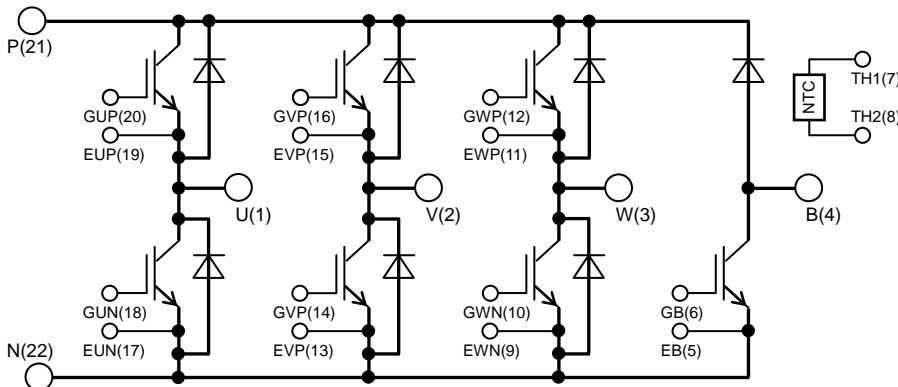
APPLICATION

AC Motor Control, Motion/Servo Control, etc.

OUTLINE DRAWING & INTERNAL CONNECTION



INTERNAL CONNECTION



Tolerance otherwise specified

| Division of Dimension | Tolerance |
|-----------------------|-----------|
| 0.5 to 3 | ±0.2 |
| over 3 to 6 | ±0.3 |
| over 6 to 30 | ±0.5 |
| over 30 to 120 | ±0.8 |
| over 120 to 400 | ±1.2 |

< IGBT MODULES >

CM150RX-24S1

HIGH POWER SWITCHING USE
INSULATED TYPE

MAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/DIODE

| Symbol | Item | Conditions | Rating | Unit |
|-------------------|---------------------------|--|----------|------|
| V_{CES} | Collector-emitter voltage | G-E short-circuited | 1200 | V |
| V_{GES} | Gate-emitter voltage | C-E short-circuited | ± 20 | V |
| I_C | Collector current | DC, $T_C=107\text{ }^\circ\text{C}$ (Note2, 4) | 150 | A |
| I_{CRM} | | Pulse, Repetitive (Note3) | 300 | |
| P_{tot} | Total power dissipation | $T_C=25\text{ }^\circ\text{C}$ (Note2, 4) | 935 | W |
| I_E (Note1) | Emitter current | DC (Note2) | 150 | A |
| I_{ERM} (Note1) | | Pulse, Repetitive (Note3) | 300 | |

BRAKE PART IGBT/DIODE

| Symbol | Item | Conditions | Rating | Unit |
|-----------|---------------------------------|--|----------|------|
| V_{CES} | Collector-emitter voltage | G-E short-circuited | 1200 | V |
| V_{GES} | Gate-emitter voltage | C-E short-circuited | ± 20 | V |
| I_C | Collector current | DC, $T_C=109\text{ }^\circ\text{C}$ (Note2, 4) | 75 | A |
| I_{CRM} | | Pulse, Repetitive (Note3) | 150 | |
| P_{tot} | Total power dissipation | $T_C=25\text{ }^\circ\text{C}$ (Note2, 4) | 480 | W |
| V_{RRM} | Repetitive peak reverse voltage | G-E short-circuited | 1200 | V |
| I_F | Forward current | DC (Note2) | 75 | A |
| I_{FRM} | | Pulse, Repetitive (Note3) | 150 | |

MODULE

| Symbol | Item | Conditions | Rating | Unit |
|------------|--------------------------------|---|------------|------------------|
| V_{isol} | Isolation voltage | Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min | 4000 | V |
| T_{jmax} | Maximum junction temperature | Instantaneous event (overload) | 175 | $^\circ\text{C}$ |
| T_{Cmax} | Maximum case temperature | (Note4) | 125 | |
| T_{jop} | Operating junction temperature | Continuous operation (under switching) | -40 ~ +150 | $^\circ\text{C}$ |
| T_{stg} | Storage temperature | - | -40 ~ +125 | |

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/DIODE

| Symbol | Item | Conditions | Limits | | | Unit | |
|---------------------------|--------------------------------------|---|---------------------------------|------|------|---------------|---|
| | | | Min. | Typ. | Max. | | |
| I_{CES} | Collector-emitter cut-off current | $V_{CE}=V_{CES}$, G-E short-circuited | - | - | 1.0 | mA | |
| I_{GES} | Gate-emitter leakage current | $V_{GE}=V_{GES}$, C-E short-circuited | - | - | 0.5 | μA | |
| $V_{GE(th)}$ | Gate-emitter threshold voltage | $I_C=15\text{ mA}$, $V_{CE}=10\text{ V}$ | 5.4 | 6.0 | 6.6 | V | |
| V_{CESat} (Terminal) | Collector-emitter saturation voltage | $I_C=150\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 1.80 | 2.25 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 2.00 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 2.05 | - | |
| V_{CESat} (Chip) | Collector-emitter saturation voltage | $I_C=150\text{ A}$, $V_{GE}=15\text{ V}$, (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 1.70 | 2.15 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 1.90 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 1.95 | - | |
| C_{ies} | Input capacitance | $V_{CE}=10\text{ V}$, G-E short-circuited | - | - | 15 | nF | |
| C_{oes} | Output capacitance | | - | - | 3.0 | | |
| C_{res} | Reverse transfer capacitance | | - | - | 0.25 | | |
| Q_G | Gate charge | $V_{CC}=600\text{ V}$, $I_C=150\text{ A}$, $V_{GE}=15\text{ V}$ | - | 315 | - | nC | |
| $t_{d(on)}$ | Turn-on delay time | $V_{CC}=600\text{ V}$, $I_C=150\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, Inductive load | - | - | 800 | ns | |
| t_r | Rise time | | - | - | 200 | | |
| $t_{d(off)}$ | Turn-off delay time | | - | - | 600 | | |
| t_f | Fall time | | - | - | 300 | | |

< IGBT MODULES >

CM150RX-24S1

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/DIODE

| Symbol | Item | Conditions | Limits | | | Unit | |
|--------------------------------|-------------------------------------|---|---------------------------------|------|------|---------------|---|
| | | | Min. | Typ. | Max. | | |
| V_{EC} (Note1) (Terminal) | Emitter-collector voltage | $I_E=150\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 2.60 | 3.40 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 2.16 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 2.10 | - | |
| V_{EC} (Note1) (Chip) | | $I_E=150\text{ A}$, G-E short-circuited, (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 2.50 | 3.30 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 2.06 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 2.00 | - | |
| t_{rr} (Note1) | Reverse recovery time | $V_{CC}=600\text{ V}$, $I_E=150\text{ A}$, $V_{GE}=\pm 15\text{ V}$, | - | - | 300 | ns | |
| Q_{rr} (Note1) | Reverse recovery charge | $R_G=0\text{ }\Omega$, Inductive load | - | 4.0 | - | μC | |
| E_{on} | Turn-on switching energy per pulse | $V_{CC}=600\text{ V}$, $I_C=I_E=150\text{ A}$, | - | 16.6 | - | mJ | |
| E_{off} | Turn-off switching energy per pulse | $V_{GE}=\pm 15\text{ V}$, $R_G=0\text{ }\Omega$, $T_j=150\text{ }^\circ\text{C}$, | - | 17.6 | - | | |
| E_{rr} (Note1) | Reverse recovery energy per pulse | Inductive load | - | 10.8 | - | | |
| $R_{CC'+EE'}$ | Internal lead resistance | Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note4) | - | - | 0.7 | m Ω | |
| r_g | Internal gate resistance | Per switch | - | 13 | - | Ω | |

BRAKE PART IGBT/DIODE

| Symbol | Item | Conditions | Limits | | | Unit | |
|------------------------|--------------------------------------|--|---------------------------------|------|------|---------------|---|
| | | | Min. | Typ. | Max. | | |
| I_{CES} | Collector-emitter cut-off current | $V_{CE}=V_{CES}$, G-E short-circuited | - | - | 1.0 | mA | |
| I_{GES} | Gate-emitter leakage current | $V_{GE}=V_{GES}$, C-E short-circuited | - | - | 0.5 | μA | |
| $V_{GE(th)}$ | Gate-emitter threshold voltage | $I_C=7.5\text{ mA}$, $V_{CE}=10\text{ V}$ | 5.4 | 6.0 | 6.6 | V | |
| V_{CESat} (Terminal) | Collector-emitter saturation voltage | $I_C=75\text{ A}$, $V_{GE}=15\text{ V}$, Refer to the figure of test circuit (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 1.80 | 2.25 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 2.00 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 2.05 | - | |
| V_{CESat} (Chip) | | $I_C=75\text{ A}$, $V_{GE}=15\text{ V}$, (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 1.70 | 2.15 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 1.90 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 1.95 | - | |
| C_{ies} | Input capacitance | $V_{CE}=10\text{ V}$, G-E short-circuited | - | - | 7.5 | nF | |
| C_{oes} | Output capacitance | | - | - | 1.5 | | |
| C_{res} | Reverse transfer capacitance | | - | - | 0.13 | | |
| Q_G | Gate charge | $V_{CC}=600\text{ V}$, $I_C=75\text{ A}$, $V_{GE}=15\text{ V}$ | - | 158 | - | nC | |
| $t_{d(on)}$ | Turn-on delay time | $V_{CC}=600\text{ V}$, $I_C=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\text{ }\Omega$, Inductive load | - | - | 300 | ns | |
| t_r | Rise time | | - | - | 200 | | |
| $t_{d(off)}$ | Turn-off delay time | | - | - | 600 | | |
| t_f | Fall time | | - | - | 300 | | |
| I_{RRM} | Repetitive peak reverse current | $V_R=V_{RRM}$, G-E short-circuited | - | - | 1.0 | mA | |
| V_F (Terminal) | Forward voltage | $I_F=75\text{ A}$, Refer to the figure of test circuit (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 2.60 | 3.40 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 2.16 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 2.10 | - | |
| V_F (Chip) | | $I_F=75\text{ A}$, (Note5) | $T_j=25\text{ }^\circ\text{C}$ | - | 2.50 | 3.30 | V |
| | | | $T_j=125\text{ }^\circ\text{C}$ | - | 2.06 | - | |
| | | | $T_j=150\text{ }^\circ\text{C}$ | - | 2.00 | - | |
| t_{rr} | Reverse recovery time | $V_{CC}=600\text{ V}$, $I_F=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, | - | - | 300 | ns | |
| Q_{rr} | Reverse recovery charge | $R_G=8.2\text{ }\Omega$, Inductive load | - | 2.0 | - | μC | |
| E_{on} | Turn-on switching energy per pulse | $V_{CC}=600\text{ V}$, $I_C=I_F=75\text{ A}$, | - | 3.5 | - | mJ | |
| E_{off} | Turn-off switching energy per pulse | $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\text{ }\Omega$, $T_j=150\text{ }^\circ\text{C}$, | - | 7.3 | - | | |
| E_{rr} | Reverse recovery energy per pulse | Inductive load | - | 6.5 | - | | |
| r_g | Internal gate resistance | - | - | 0 | - | Ω | |

< IGBT MODULES >

CM150RX-24S1

HIGH POWER SWITCHING USE
INSULATED TYPE

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)

NTC THERMISTOR PART

| Symbol | Item | Conditions | Limits | | | Unit |
|----------------------|-------------------------|---|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| R ₂₅ | Zero-power resistance | T _C =25 °C (Note4) | 4.85 | 5.00 | 5.15 | kΩ |
| ΔR/R | Deviation of resistance | R ₁₀₀ =493 Ω, T _C =100 °C (Note4) | -7.3 | - | +7.8 | % |
| B _(25/50) | B-constant | Approximate by equation (Note6) | - | 3375 | - | K |
| P ₂₅ | Power dissipation | T _C =25 °C (Note4) | - | - | 10 | mW |

THERMAL RESISTANCE CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|-----------------------|----------------------------|--|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| R _{th(j-c)Q} | Thermal resistance | Junction to case, per Inverter IGBT (Note4) | - | - | 0.16 | K/W |
| R _{th(j-c)D} | | Junction to case, per Inverter DIODE (Note4) | - | - | 0.26 | |
| R _{th(j-c)Q} | | Junction to case, per Brake IGBT (Note4) | - | - | 0.31 | K/W |
| R _{th(j-c)D} | | Junction to case, per Brake DIODE (Note4) | - | - | 0.47 | |
| R _{th(c-s)} | Contact thermal resistance | Case to heat sink, per 1 module, Thermal grease applied (Note4,7) | - | 15 | - | K/kW |

MECHANICAL CHARACTERISTICS

| Symbol | Item | Conditions | Limits | | | Unit |
|----------------|------------------------|---------------------------------|--------|------|------|------|
| | | | Min. | Typ. | Max. | |
| M _t | Mounting torque | Main terminals M 5 screw | 2.5 | 3.0 | 3.5 | N·m |
| M _s | Mounting torque | Mounting to heat sink M 5 screw | 2.5 | 3.0 | 3.5 | N·m |
| d _s | Creepage distance | Terminal to terminal | 17 | - | - | mm |
| | | Terminal to base plate | 20.1 | - | - | |
| d _a | Clearance | Terminal to terminal | 10 | - | - | mm |
| | | Terminal to base plate | 14.8 | - | - | |
| m | mass | - | - | 370 | - | g |
| e _c | Flatness of base plate | On the centerline X, Y (Note8) | ±0 | - | +100 | μm |

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (DIODE).

- Junction temperature (T_j) should not increase beyond T_{jmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.
- Case temperature (T_C) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise.

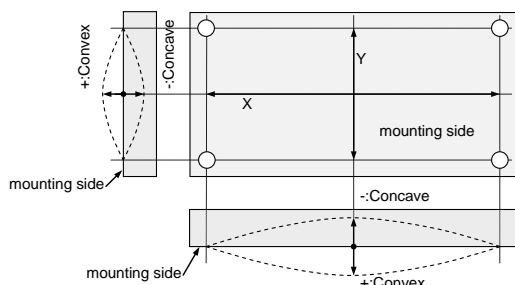
$$6. B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right),$$

R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]

R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]

7. Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).

8. The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



9. Use the following screws when mounting the printed circuit board (PCB) on the stand offs.

"φ2.6×10 or φ2.6×12 B1 tapping screw"

The length of the screw depends on the thickness (t1.6~t2.0) of the PCB.

< IGBT MODULES >

CM150RX-24S1

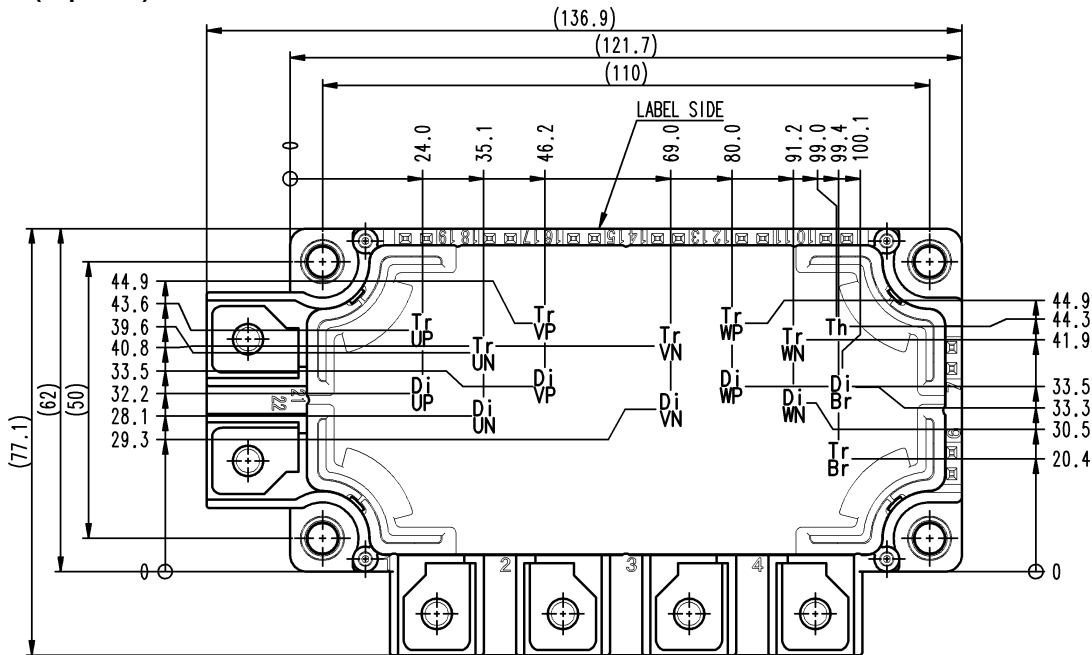
HIGH POWER SWITCHING USE
INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS

| Symbol | Item | Conditions | Limits | | | Unit | |
|------------|-------------------------------|---|---------------|------|------|------|----------|
| | | | Min. | Typ. | Max. | | |
| V_{CC} | (DC) Supply voltage | Applied across P-N terminals | - | 600 | 850 | V | |
| V_{GEon} | Gate (-emitter drive) voltage | Applied across GB-EB/ G*P-E*P/G*N-E*N(*=U, V, W) terminals | 13.5 | 15.0 | 16.5 | V | |
| R_G | External gate resistance | Per switch | Inverter IGBT | 0 | - | 30 | Ω |
| | | | Brake IGBT | 8.2 | - | 82 | |

CHIP LOCATION (Top view)

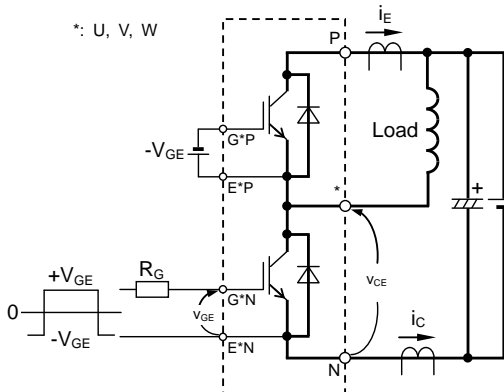
Dimension in mm, tolerance: ± 1 mm



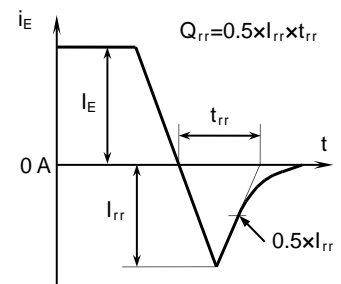
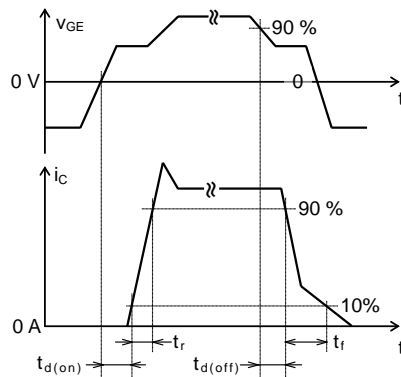
Tr*P/Tr*N/TrBr: IGBT, Di*P/Di*N: DIODE (*=U/V/W), DiBr: Brake DIODE, Th: NTC thermistor

TEST CIRCUIT AND WAVEFORMS

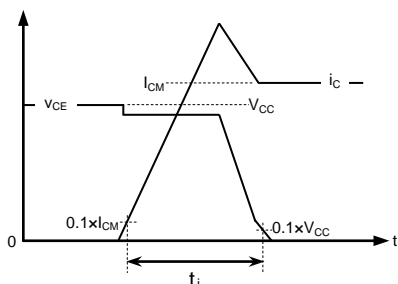
*: U, V, W



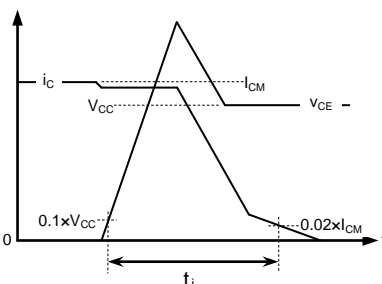
Switching test circuit and waveforms



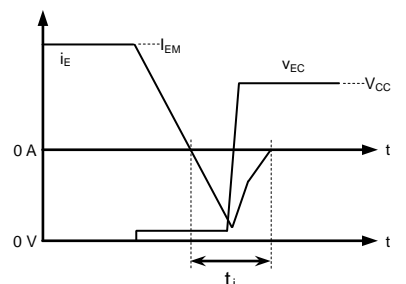
t_{rr} , Q_{rr} characteristics test waveform



IGBT Turn-on switching energy



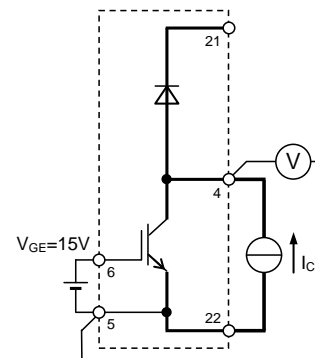
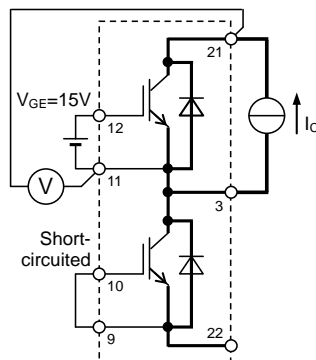
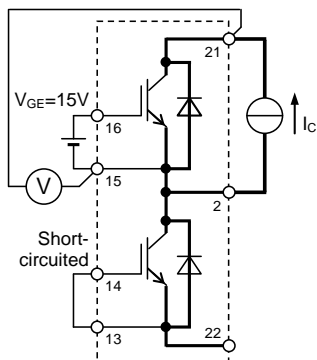
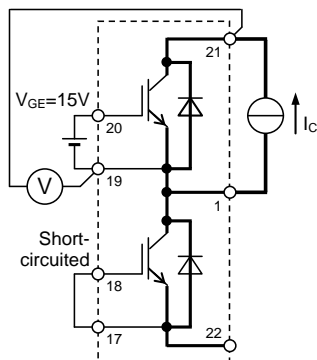
IGBT Turn-off switching energy



DIODE Reverse recovery energy

Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT



Gate-emitter GVP-EVP, GVN-EVN,
short-circuited GWP-EWP, GWN-EWN,
GB-EB

UP / UN IGBT

Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN,
GB-EB

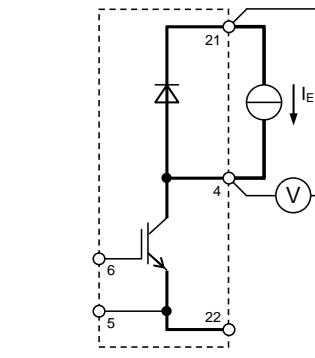
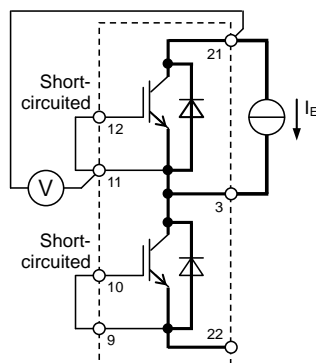
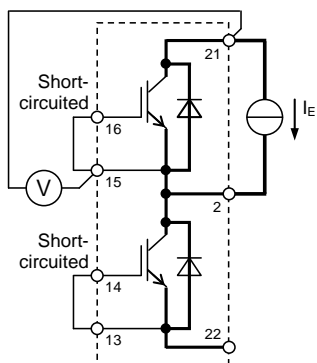
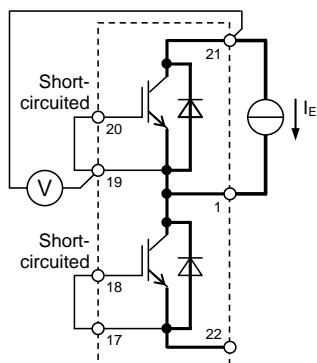
VP / VN IGBT

Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN,
GB-EB

WP / WN IGBT

Brake IGBT

V_{CEsat} characteristics test circuit



Gate-emitter GVP-EVP, GVN-EVN,
short-circuited GWP-EWP, GWN-EWN,
GB-EB

UP / UN DIODE

Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GWP-EWP, GWN-EWN,
GB-EB

VP / VN DIODE

Gate-emitter GUP-EUP, GUN-EUN,
short-circuited GVP-EVP, GVN-EVN,
GB-EB

WP / WN DIODE

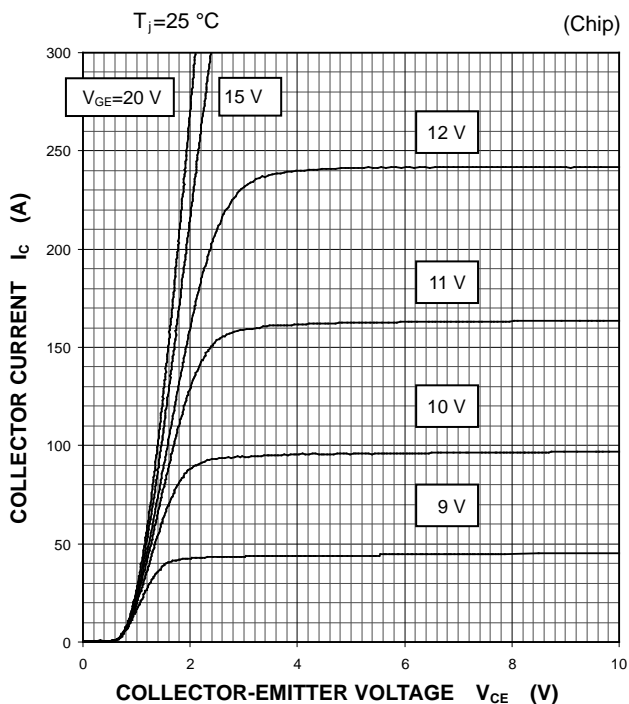
Brake DIODE

V_{EC} / V_F characteristics test circuit

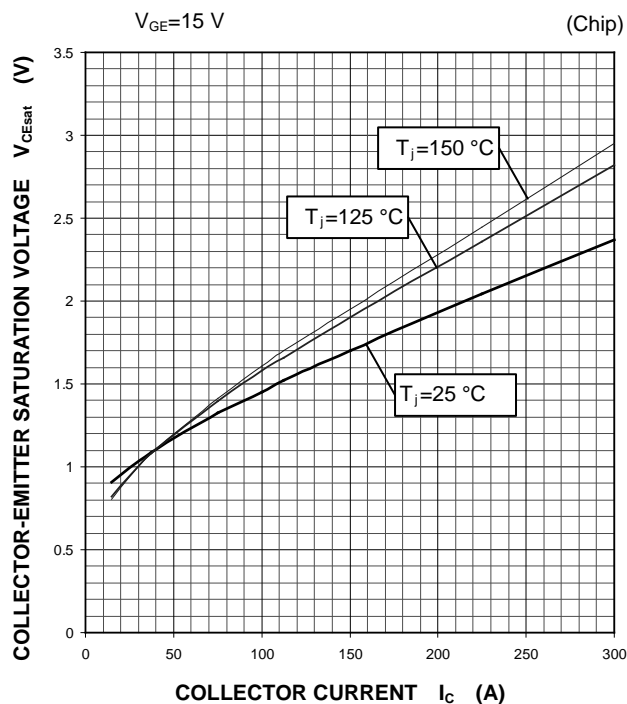
PERFORMANCE CURVES

INVERTER PART

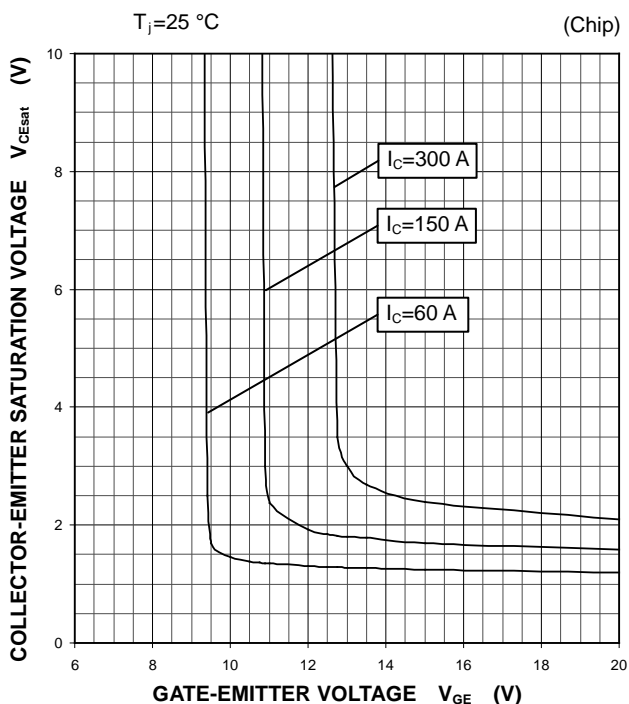
OUTPUT CHARACTERISTICS
(TYPICAL)



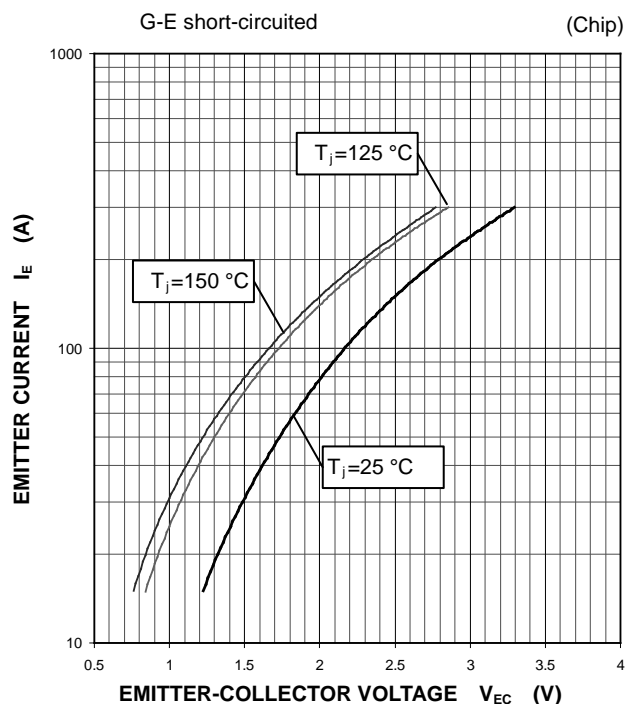
COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)



FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



< IGBT MODULES >
CM150RX-24S1

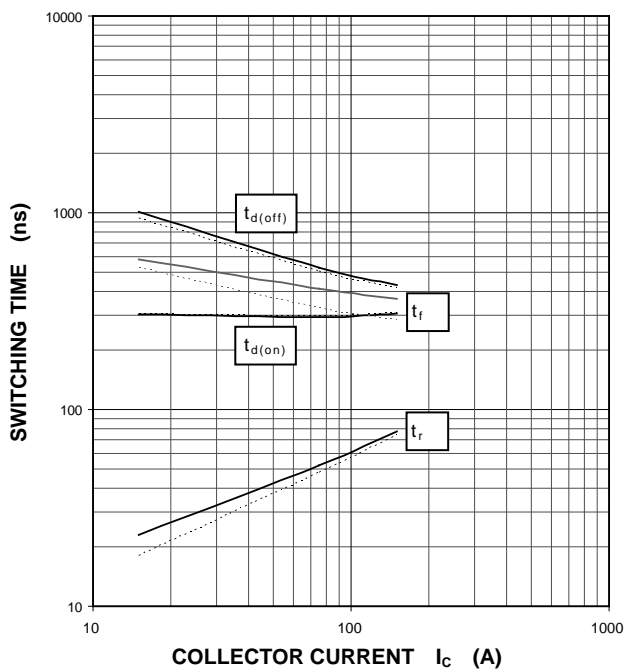
**HIGH POWER SWITCHING USE
 INSULATED TYPE**

PERFORMANCE CURVES

INVERTER PART

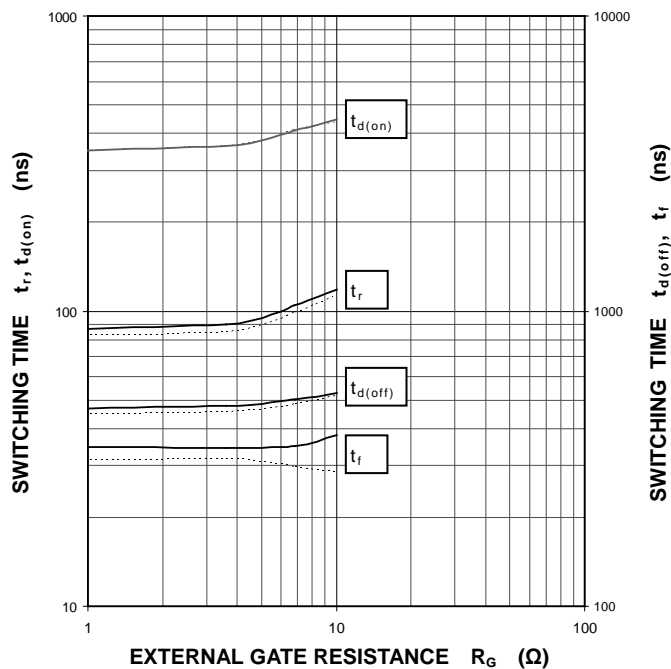
**HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



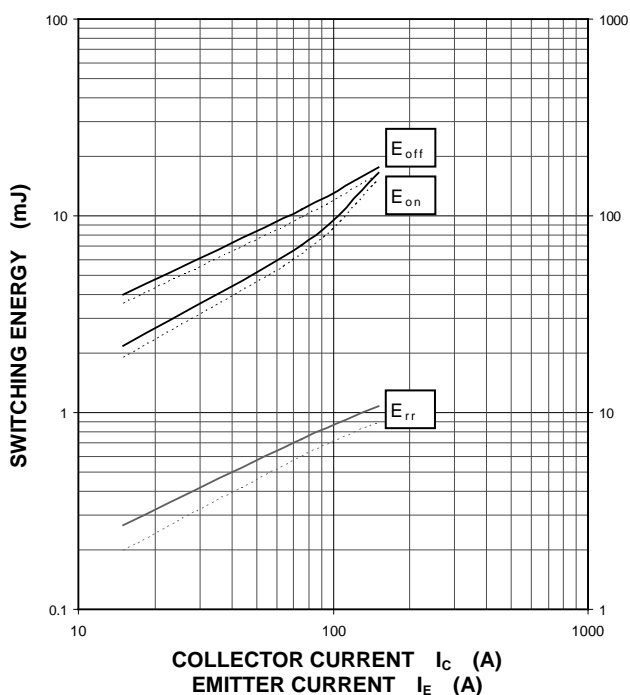
**HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=150\text{ A}$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



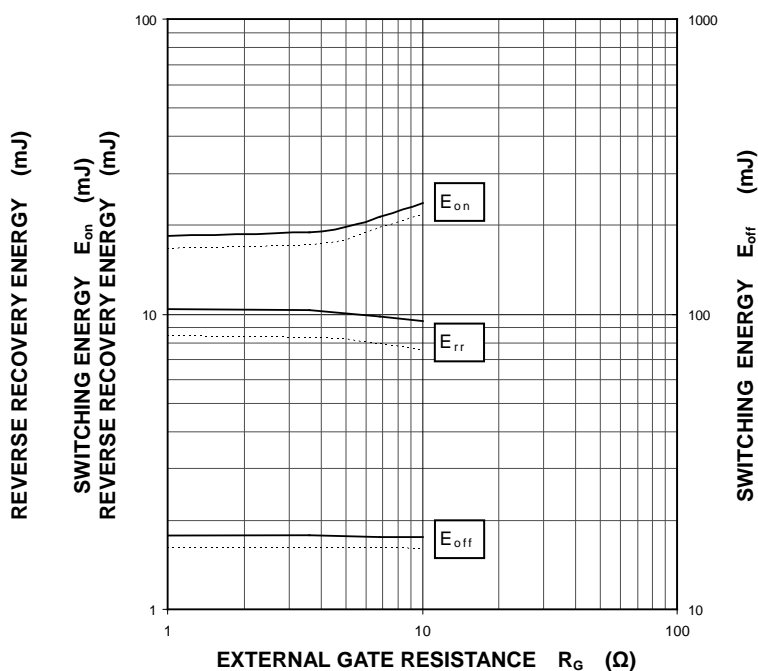
**HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$,
 INDUCTIVE LOAD, PER PULSE
 —: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



**HALF-BRIDGE
 SWITCHING CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C/I_E=150\text{ A}$,
 INDUCTIVE LOAD, PER PULSE
 —: $T_j=150\text{ }^\circ\text{C}$, - - - - -: $T_j=125\text{ }^\circ\text{C}$



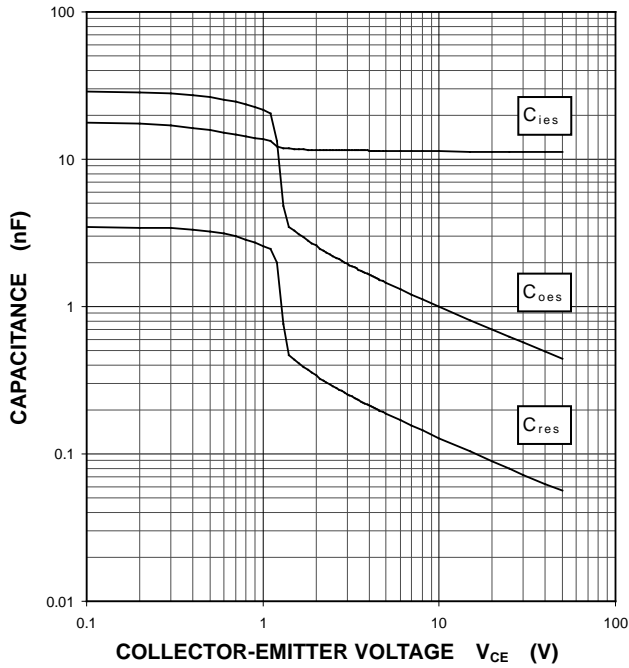
< IGBT MODULES >
CM150RX-24S1
 HIGH POWER SWITCHING USE
 INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

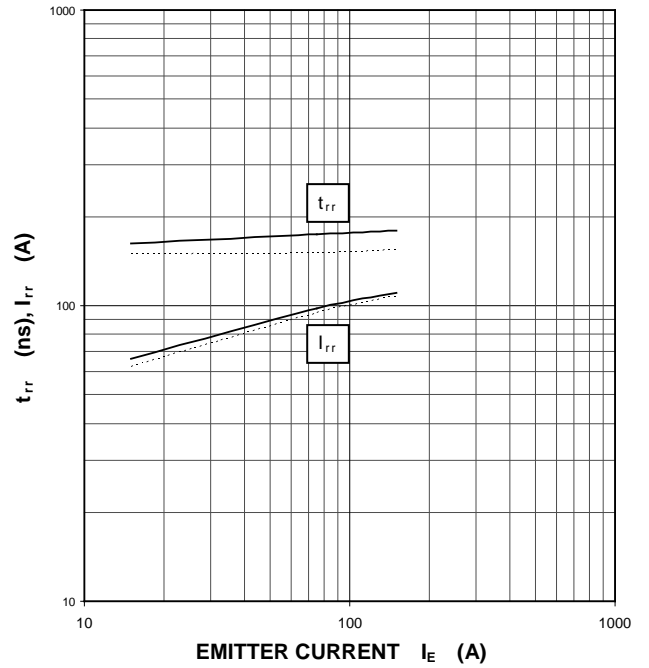
**CAPACITANCE CHARACTERISTICS
 (TYPICAL)**

G-E short-circuited, $T_j=25\text{ }^\circ\text{C}$



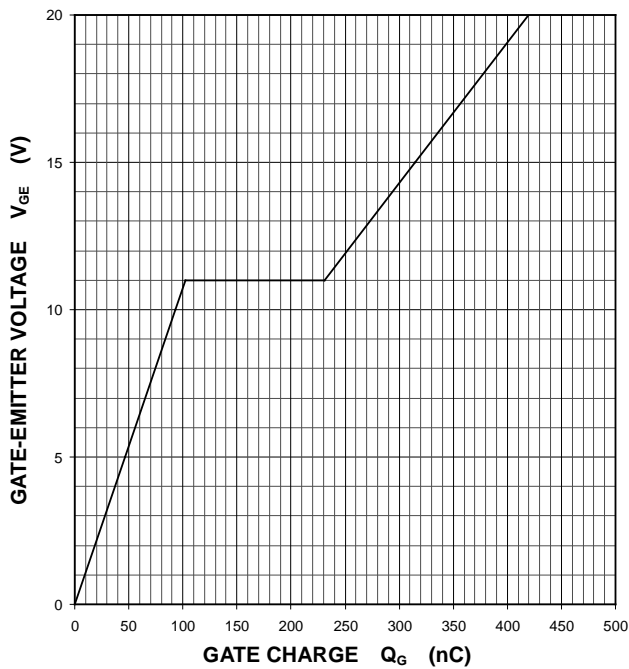
**FREE WHEELING DIODE
 REVERSE RECOVERY CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0\ \Omega$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



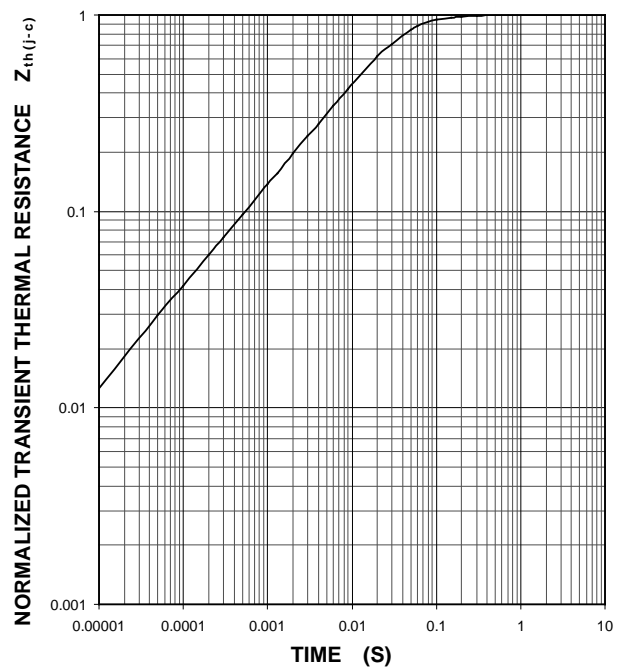
**GATE CHARGE CHARACTERISTICS
 (TYPICAL)**

$V_{CC}=600\text{ V}$, $I_C=150\text{ A}$, $T_j=25\text{ }^\circ\text{C}$



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
 (MAXIMUM)**

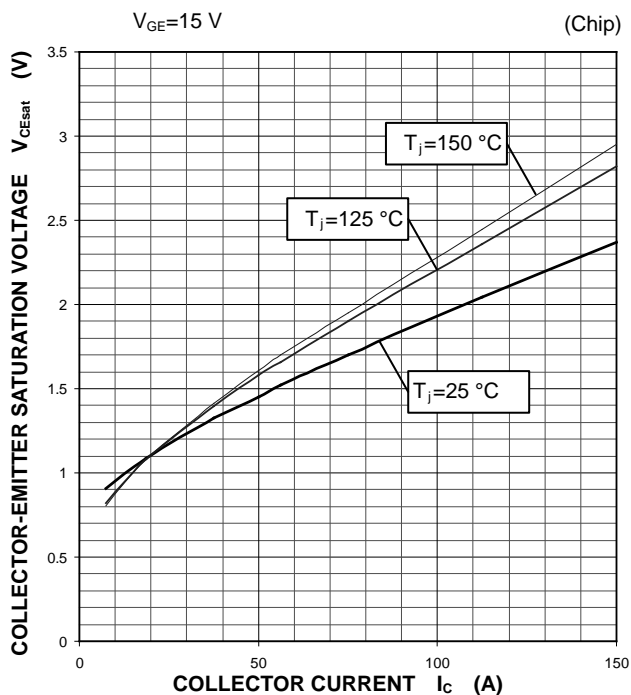
Single pulse, $T_C=25\text{ }^\circ\text{C}$
 $R_{th(j-c)Q}=0.16\text{ K/W}$, $R_{th(j-c)D}=0.26\text{ K/W}$



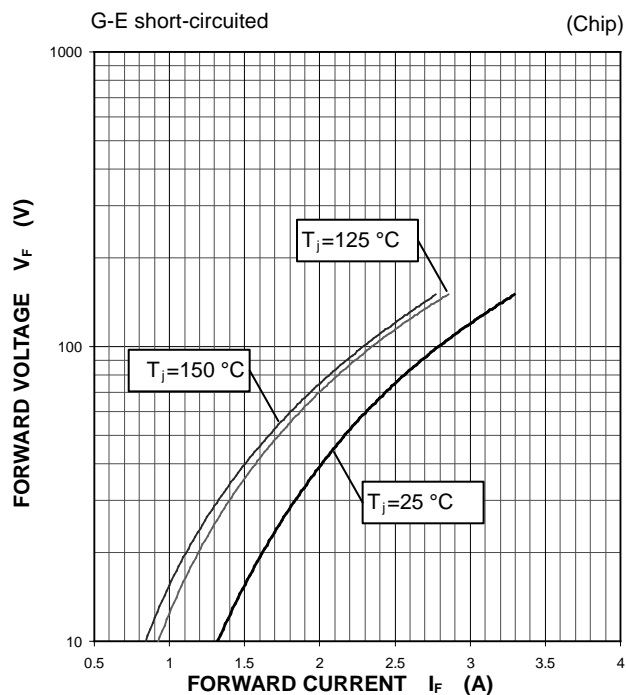
PERFORMANCE CURVES

BRAKE PART

COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)

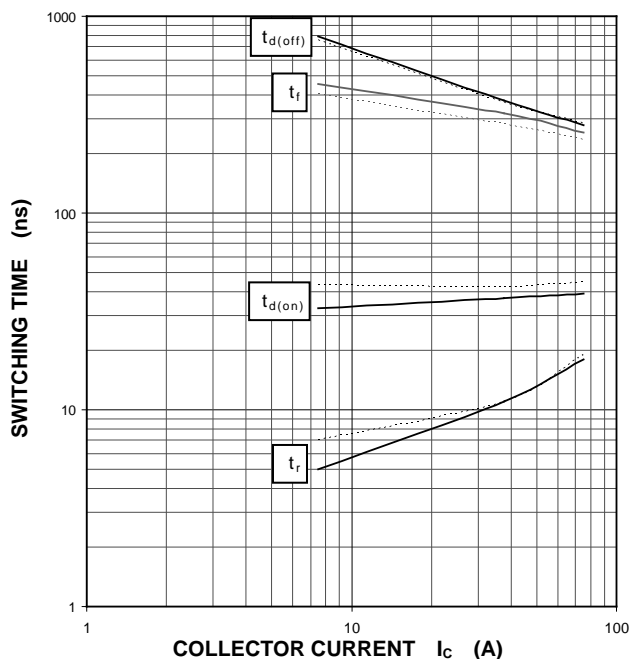


CLAMP DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



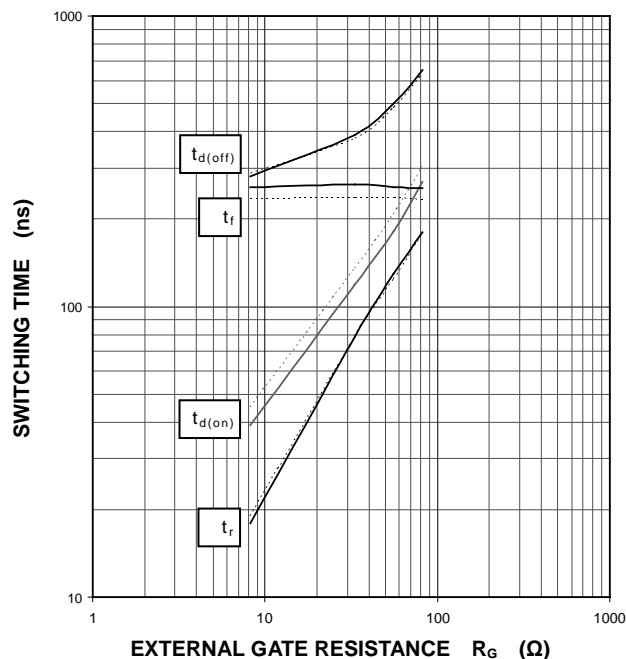
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\ \Omega$, INDUCTIVE LOAD
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $I_C=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
——: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



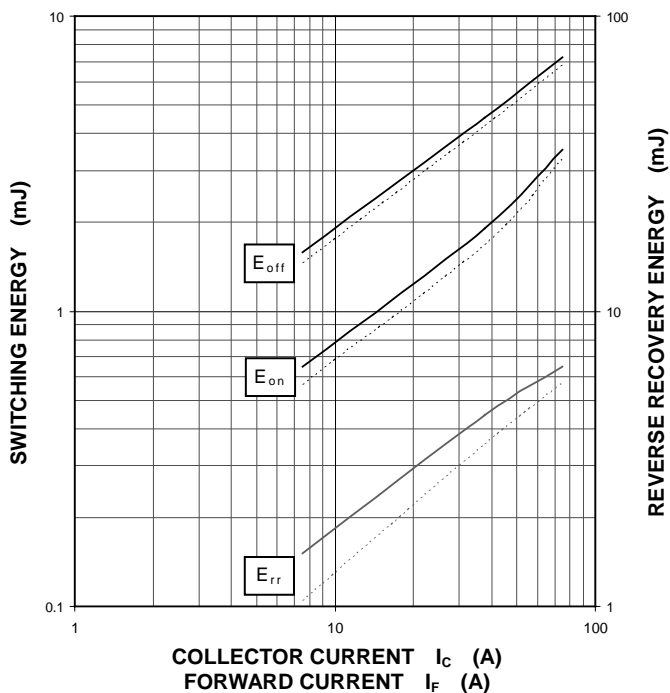
< IGBT MODULES >
CM150RX-24S1

HIGH POWER SWITCHING USE
 INSULATED TYPE

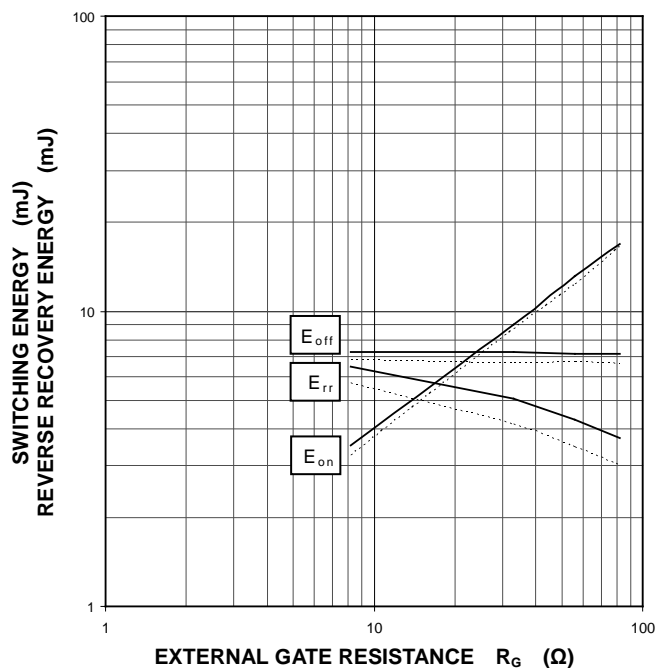
PERFORMANCE CURVES

BRAKE PART

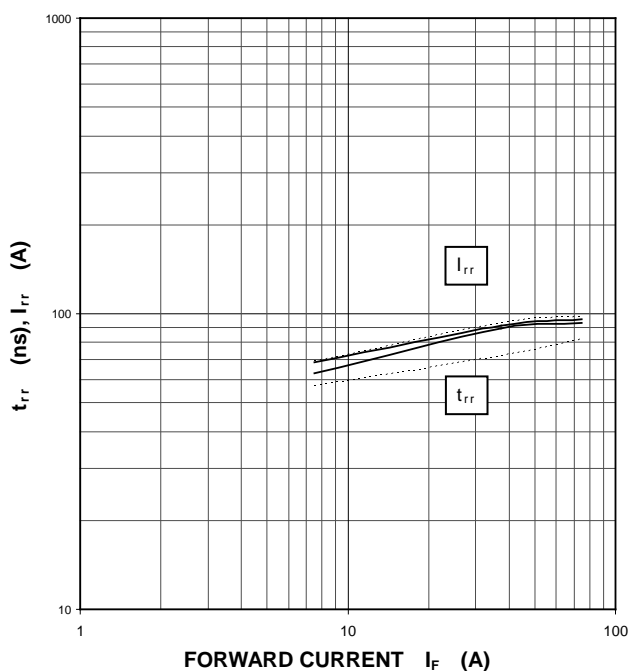
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)
 $V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\ \Omega$,
 INDUCTIVE LOAD, PER PULSE
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



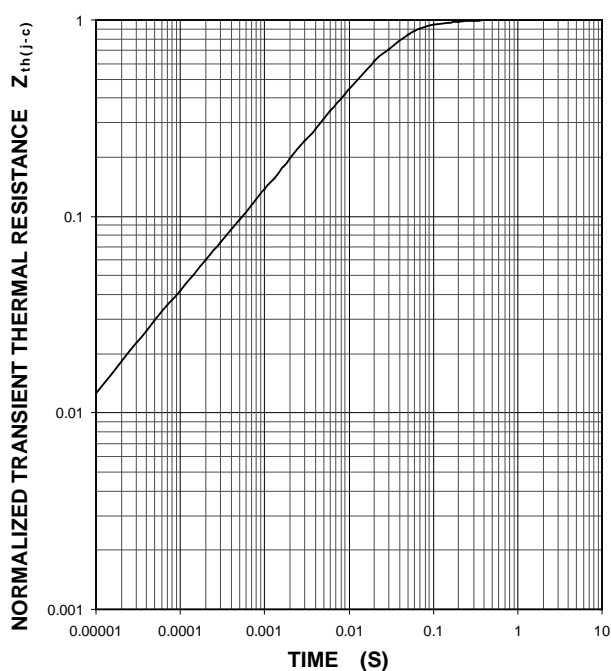
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)
 $V_{CC}=600\text{ V}$, $I_C/I_F=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
 INDUCTIVE LOAD, PER PULSE
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



CLAMP DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)
 $V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=8.2\ \Omega$, INDUCTIVE LOAD
 —: $T_j=150\text{ }^\circ\text{C}$, - - - -: $T_j=125\text{ }^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)
 Single pulse, $T_C=25\text{ }^\circ\text{C}$
 $R_{th(j-c)Q}=0.31\text{ K/W}$, $R_{th(j-c)D}=0.47\text{ K/W}$

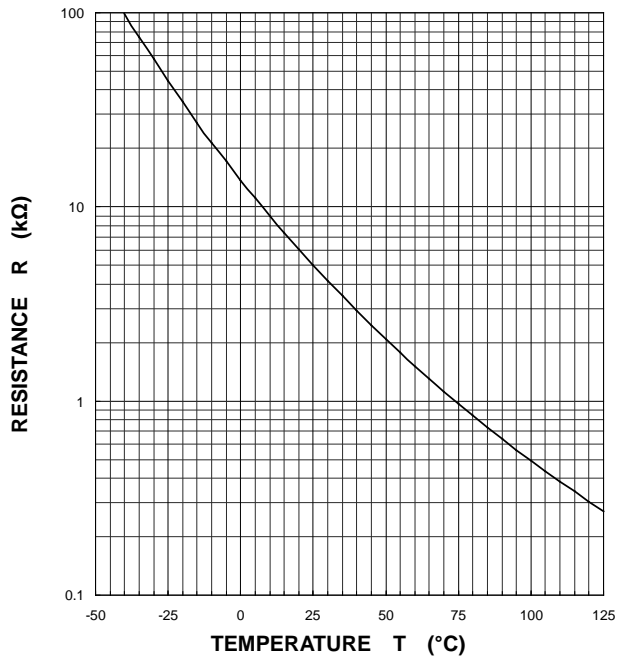


< IGBT MODULES >
CM150RX-24S1
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part

TEMPERATURE CHARACTERISTICS
(TYPICAL)



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